

*D1010

*PSPICE MODEL FOR POINT NINE RF N-CHANNEL VERTICAL DMOS POWER FET

*May 2004

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*          _____GATE
*          I   _____DRAIN
*          I   I   _____SOURCE
*          I   I   I
.SUBCKT D1010  10  20  30
*   Cin1,Cin2 & Lin model the input side of the package
Cin1  10   30   0.79p
Lin   10   11   0.38n
Cin2  11   30   0.79p
LG    11   12   0.6n      ;Gate bond wire inductance
CGS   12   13   184p     ;Gate-source capacitance
MOS   14   12   13      13 D1010 L=0.9U W=0.224      ;D G S B
LEVEL1
JFET  16   13   14      D1010                      ;D G S
DBODY 13   16      D1010                      ;P N
LS    13   30   0.2n    ;Source bond wire inductance
CGD   12   16   4p      ;Gate-drain feedback capacitance
*   Cout1,Cout2 & Lout model the output side of the package
Cout1 16   30   1.38p
Lout   16   20   0.73n
Cout2 20   30   1.15p

.MODEL D1010 NMOS (VTO=4.76 KP=2.81E-5 LAMBDA=0.032 RD=0.019 RS=0.077)
.MODEL D1010 NJF (VTO=-4.3 BETA=1 LAMBDA=0.54)
.MODEL D1010 D (CJO=328.8P RS=0.25 VJ=0.7 M=0.35 BV=75)

.ENDS
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